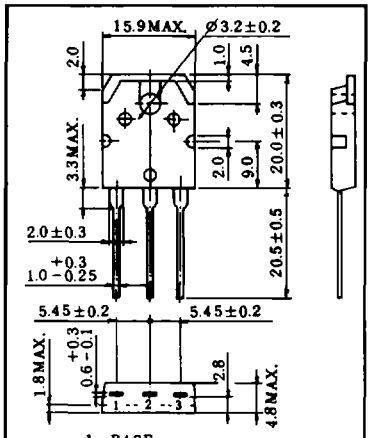
SILICON PNP TRIPLE DIFFUSED TYPE

2SA1263N

POWER AMPLIFIER APPLICATIONS.

- Complementary to 2SC3180N
- Recommend for 40W High Fiderity Audio Frequency Amplifier Output Stage.

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-16C1A

Weight : 4.7g

MAXIMUM RATINGS (Ta=25°C)

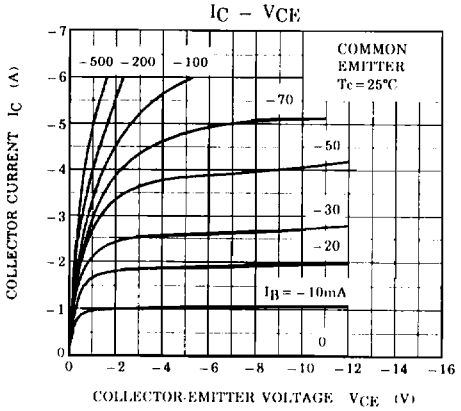
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-6	A
Base Current	I_B	-0.6	A
Collector Power Dissipation (Tc=25°C)	P_C	60	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

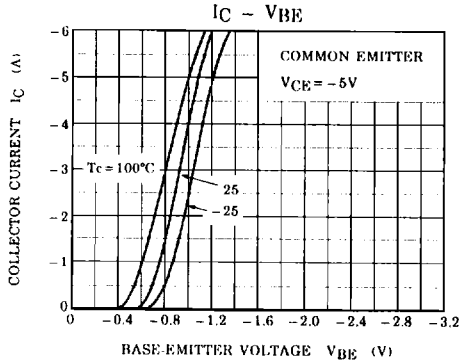
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-80V, I_E=0	-	-	-5.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-50mA, I_B=0	-80	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	V_{CE}=-5V, I_C=-1A	55	-	160	-
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-3A	35	80	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-5A, I_B=-0.5A	-	-1.0	-2.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-3A	-	-0.95	-1.5	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-1A	-	30	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	290	-	pF

Note : $h_{FE(1)}$ Classification R : 55~110 O : 80~160

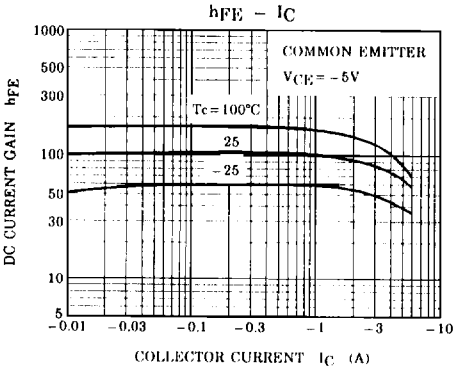
I_C – V_{CE}



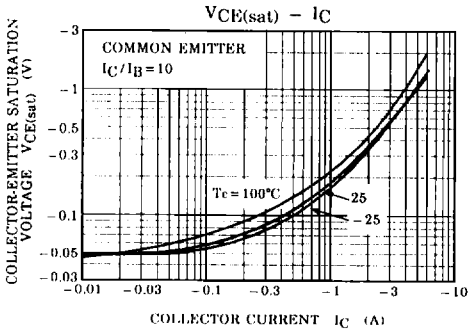
I_C – V_{BE}



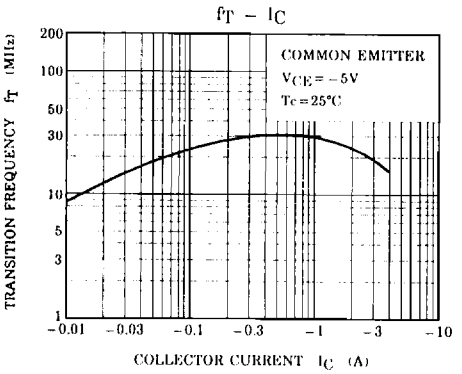
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



f_T – I_C



SAFE OPERATING AREA